

Power MOSFET

PRODUCT SUMMARY

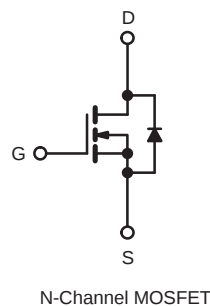
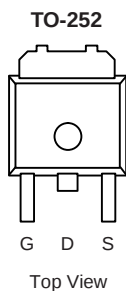
V_{DS} (V)	650	
$R_{DS(on)}$ (Ω)	$V_{GS} = 10\text{ V}$	2.1
Q_g (Max.) (nC)	48	
Q_{gs} (nC)	12	
Q_{gd} (nC)	19	
Configuration	Single	

FEATURES

- Low Gate Charge Q_g Results in Simple Drive Requirement
- Improved Gate, Avalanche and Dynamic dV/dt Ruggedness
- Fully Characterized Capacitance and Avalanche Voltage and Current
- Compliant to RoHS directive 2002/95/EC



RoHS*
COMPLIANT



ABSOLUTE MAXIMUM RATINGS $T_C = 25\text{ }^\circ\text{C}$, unless otherwise noted

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	650	V
Gate-Source Voltage	V_{GS}	± 30	
Continuous Drain Current ^e	I_D	$T_C = 25\text{ }^\circ\text{C}$	A
Continuous Drain Current		$T_C = 100\text{ }^\circ\text{C}$	
Pulsed Drain Current ^a	I_{DM}	18	
Linear Derating Factor		0.48	W/ $^\circ\text{C}$
Single Pulse Avalanche Energy ^b	E_{AS}	325	mJ
Repetitive Avalanche Current ^a	I_{AR}	4	A
Repetitive Avalanche Energy ^a	E_{AR}	6	mJ
Maximum Power Dissipation	P_D	60	W
Peak Diode Recovery dV/dt ^c	dV/dt	2.8	V/ns
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 150	$^\circ\text{C}$
Soldering Recommendations (Peak Temperature) ^d		300	
Mounting Torque	6-32 or M3 screw	10	lbf · in
		1.1	N · m

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- Starting $T_J = 25\text{ }^\circ\text{C}$, $L = 24\text{ mH}$, $R_G = 25\text{ }\Omega$, $I_{AS} = 3.2\text{ A}$ (see fig. 12).
- $I_{SD} \leq 3.2\text{ A}$, $dI/dt \leq 90\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DS}$, $T_J \leq 150\text{ }^\circ\text{C}$.
- 1.6 mm from case.
- Drain current limited by maximum junction temperature.

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	65	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	-	2.1	

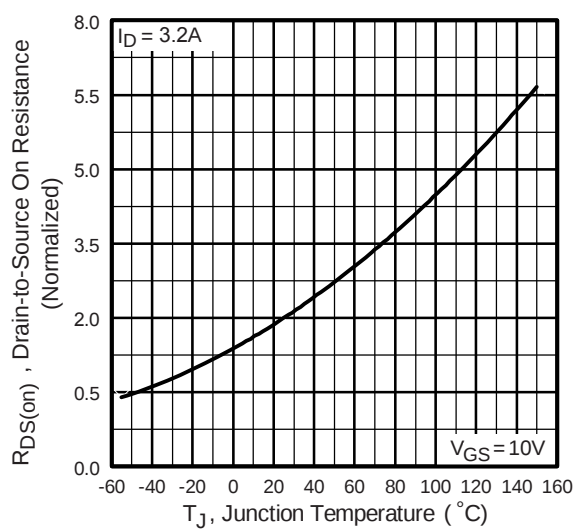
SPECIFICATIONS $T_J = 25^\circ\text{C}$, unless otherwise noted

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	650	-	-	V	
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to 25°C , $I_D = 1\text{ mA}^d$	-	670	-	mV/°C	
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2.5	-	5.0	V	
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 30\text{ V}$	-	-	± 100	nA	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 650\text{ V}, V_{GS} = 0\text{ V}$	-	-	25	μA	
		$V_{DS} = 520\text{ V}, V_{GS} = 0\text{ V}, T_J = 125^\circ\text{C}$	-	-	250		
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 3.1\text{ A}^b$	-	2.1	-	Ω	
Forward Transconductance	g_{fs}	$V_{DS} = 50\text{ V}, I_D = 3.1\text{ A}$	3.9	-	-	S	
Dynamic							
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V},$ $V_{DS} = 25\text{ V},$ $f = 1.0\text{ MHz}$, see fig. 5	-	1417	-	pF	
Output Capacitance	C_{oss}		-	177	-		
Reverse Transfer Capacitance	C_{rss}		-	7.0	-		
Output Capacitance	C_{oss}	$V_{GS} = 0\text{ V}$	$V_{DS} = 1.0\text{ V}, f = 1.0\text{ MHz}$	-	1912	-	-
			$V_{DS} = 520\text{ V}, f = 1.0\text{ MHz}$	-	48		
Effective Output Capacitance	$C_{oss\text{ eff.}}$	$V_{DS} = 0\text{ V to } 520\text{ V}^c$	-	84	-	-	-
Total Gate Charge	Q_g	$V_{GS} = 10\text{ V}$	$I_D = 3.2\text{ A}, V_{DS} = 400\text{ V}$ see fig. 6 and 13 ^b	-	-	48	nC
Gate-Source Charge	Q_{gs}			-	-	12	
Gate-Drain Charge	Q_{gd}			-	-	19	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 325\text{ V}, I_D = 3.2\text{ A}$ $R_G = 9.1\text{ }\Omega, R_D = 62\text{ }\Omega,$ see fig. 10 ^b		-	14	-	ns
Rise Time	t_r			-	20	-	
Turn-Off Delay Time	$t_{d(off)}$			-	34	-	
Fall Time	t_f			-	18	-	
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	4	A	
Pulsed Diode Forward Current ^a	I_{SM}		-	-	21		
Body Diode Voltage	V_{SD}	$T_J = 25^\circ\text{C}, I_S = 3.2\text{ A}, V_{GS} = 0\text{ V}^b$	-	-	1.5	V	
Body Diode Reverse Recovery Time	t_{rr}	$T_J = 25^\circ\text{C}, I_F = 3.2\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}^b$	-	493	739	ns	
Body Diode Reverse Recovery Charge	Q_{rr}		-	2.1	3.2	μC	
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)					

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.
- $C_{oss\text{ eff.}}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DS} .
- $t = 60\text{ s}, f = 60\text{ Hz}$.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



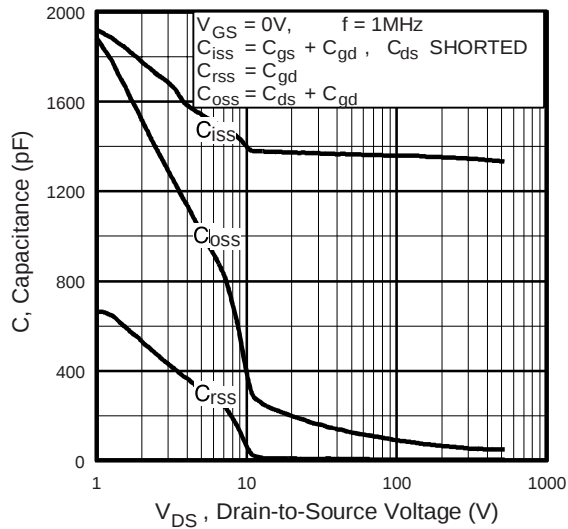


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage



Fig. 7 - Typical Source-Drain Diode Forward Voltage



Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

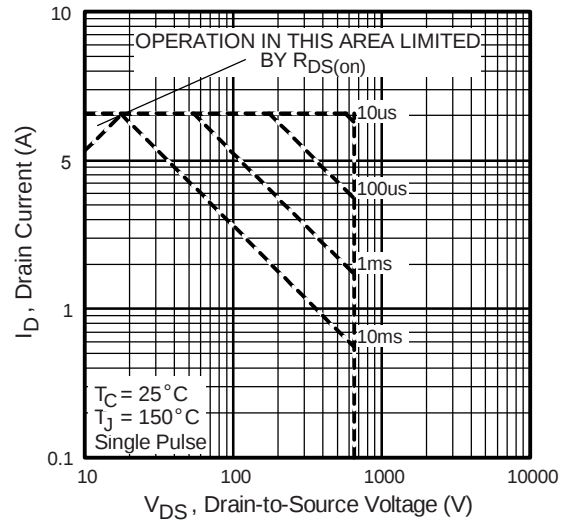


Fig. 8 - Maximum Safe Operating Area



Fig. 9 - Maximum Drain Current vs. Case Temperature



Fig. 10a - Switching Time Test Circuit



Fig. 10b - Switching Time Waveforms

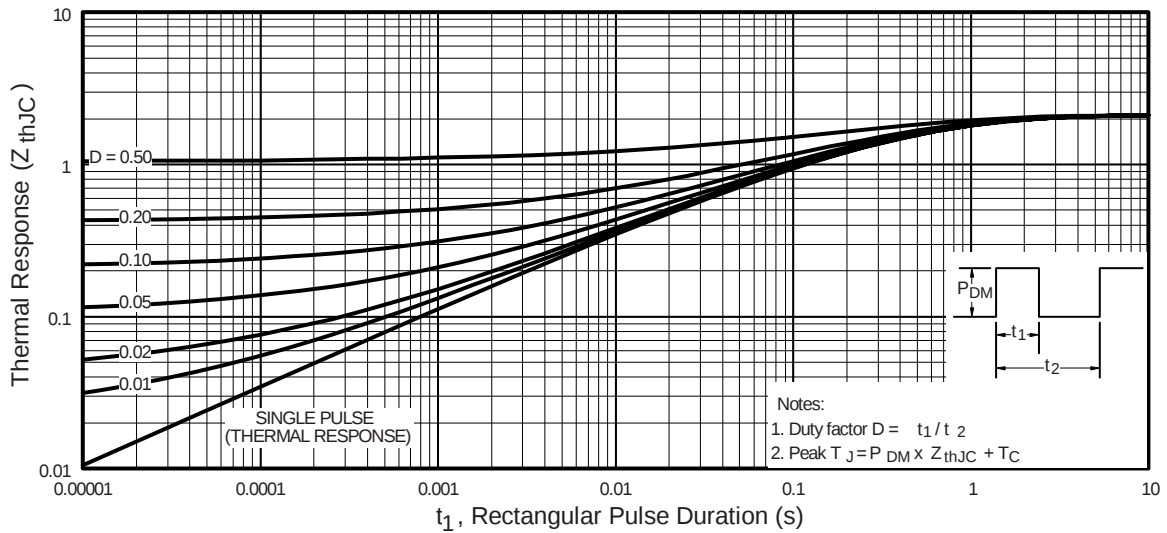


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case



Fig. 12a - Unclamped Inductive Test Circuit

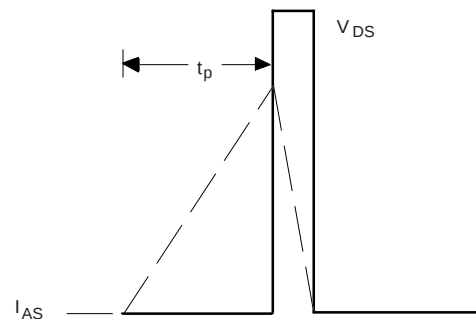


Fig. 12b - Unclamped Inductive Waveforms

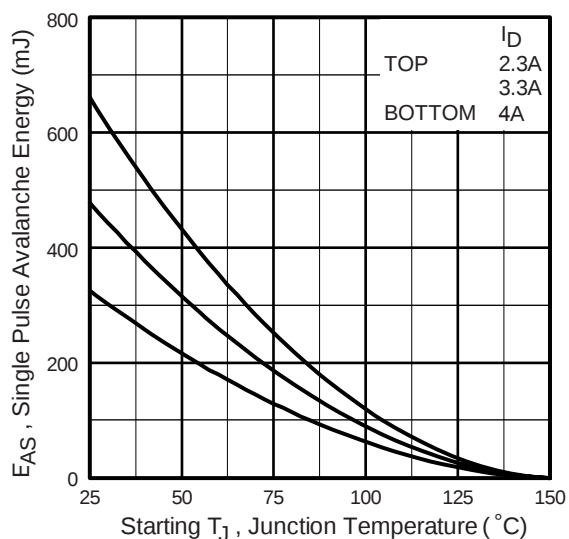


Fig. 12c - Maximum Avalanche Energy vs. Drain Current



Fig. 12d - Typical Drain-to Source Voltage vs. Avalanche Current



Fig. 13a - Basic Gate Charge Waveform



Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



* $V_{GS} = 5 V$ for logic level devices

Fig. 14 - For N-Channel

TO-252AA CASE OUTLINE



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	2.18	2.38	0.086	0.094
A1	-	0.127	-	0.005
b	0.64	0.88	0.025	0.035
b2	0.76	1.14	0.030	0.045
b3	4.95	5.46	0.195	0.215
C	0.46	0.61	0.018	0.024
C2	0.46	0.89	0.018	0.035
D	5.97	6.22	0.235	0.245
D1	5.21	-	0.205	-
E	6.35	6.73	0.250	0.265
E1	4.32	-	0.170	-
H	9.40	10.41	0.370	0.410
e	2.28 BSC		0.090 BSC	
e1	4.56 BSC		0.180 BSC	
L	1.40	1.78	0.055	0.070
L3	0.89	1.27	0.035	0.050
L4	-	1.02	-	0.040
L5	1.14	1.52	0.045	0.060
ECN: X12-0247-Rev. M, 24-Dec-12 DWG: 5347				

Note

- Dimension L3 is for reference only.

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